

Calculation

- Input Voltage - 0.2 to 0.5 volt, That is peak to peak Voltage.

- NE555 Set as astable Mode for 100kHz Freq.

$$C = 1\text{nf}$$

$$R_1 = 2.2\text{k}\Omega$$

$$R_2 = 5\text{k}\Omega$$

- Because $T = 0.7(R_1 + 2R_2) \times C$
Need $f = 100\text{kHz}$ $\therefore T = 10^{-5}\text{sec}$

- For Integrator

$$\text{Gain} = \frac{1}{j2\pi f R_1 C_f}$$

$$\text{Gain} = 1 \text{ hence,}$$

$$R_1 C_f = 1.59 \times 10^{-5}\text{s}$$

$$R_1 = 10\text{k}\Omega$$

$$C_f = 1.2\text{nF}$$

- For MOSFET Need

- $V_{gs} > V_{th}$ Need.

for that $\rightarrow V_{gs} = V_{gate} - V_{source}$

For high side N-MOSFET

$$V_{source} = \text{Output} = 0 \text{ to } 12 \text{ volt}$$

For that high side N-MOSFET Need to V_{gs} Voltage higher than 12 volt.

That's why we added Bootstrapping Circuit.

Make gate Voltage Greater than 12V.

Add Bootstrap.

• Low pass filter -

$$F_{PWM} = 100 \text{ kHz}$$

But After low pass filter

$$\text{we get } f_c = 30 \text{ kHz}, R_L = 8 \Omega$$

then
$$L = \frac{R_L}{2\pi f_c}$$

$$L = 62.44 \mu\text{H}$$

$$\underline{\underline{L \approx 67 \mu\text{H}}}$$

f

$$C = \frac{1}{2\pi f_c R_L}$$

$$\underline{\underline{C = 2.2 \mu\text{F}}}$$

Hence we get 5Watt output.